BCW68GL

General Purpose Transistor

PNP Silicon

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

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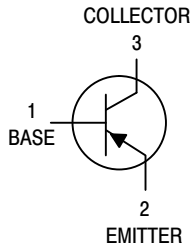
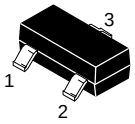




SOT−23
CASE 318
STYLE 6

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	−45	Vdc
Collector−Base Voltage	V_{CBO}	−60	Vdc
Emitter−Base Voltage	V_{EBO}	−5.0	Vdc
Collector Current − Continuous	I_C	−800	mAdc

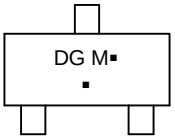
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in 99.5% alumina.

MARKING DIAGRAM



DG = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BCW68GLT1G, NSVBCW68GLT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
BCW68GLT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (I_C = −10 mAdc, I_B = 0)	$V_{(BR)CEO}$	−45	−	−	Vdc
Collector−Emitter Breakdown Voltage (I_C = −10 μAdc, V_{EB} = 0)	$V_{(BR)CES}$	−60	−	−	Vdc
Emitter−Base Breakdown Voltage (I_E = −10 μAdc, I_C = 0)	$V_{(BR)EBO}$	−5.0	−	−	Vdc
Collector Cutoff Current (V_{CE}= −45 Vdc, I_E = 0) (V_{CE}= −45 Vdc, I_B = 0, T_A = 150°C)	I_{CES}	 − −	 − −	 −20 −10	 nAdc μAdc
Emitter Cutoff Current (V_{EB} = −4.0 Vdc, I_C = 0)	I_{EBO}	−	−	−20	nAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = −10 mAdc, V_{CE} = −1.0 Vdc) (I_C = −100 mAdc, V_{CE} = −1.0 Vdc) (I_C = −300 mAdc, V_{CE} = −1.0 Vdc)	h_{FE}	 120 160 60	 − − −	 400 − −	−
Collector−Emitter Saturation Voltage (I_C = −500 mAdc, I_B = −50 mAdc)	$V_{CE(sat)}$	−	−	−0.7	Vdc
Base−Emitter Saturation Voltage (I_C = −500 mAdc, I_B = −50 mAdc)	$V_{BE(sat)}$	−	−	−2.0	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = −20 mAdc, V_{CE} = −10 Vdc, f = 100 MHz)	f_T	100	−	−	MHz
Output Capacitance (V_{CB}= −10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	−	−	18	pF
Input Capacitance (V_{EB}= −0.5 Vdc, I_C = 0, f = 1.0 MHz)	C_{ibo}	−	−	105	pF
Noise Figure (I_C= −0.2 mAdc, V_{CE} = −5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	N_F	−	−	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

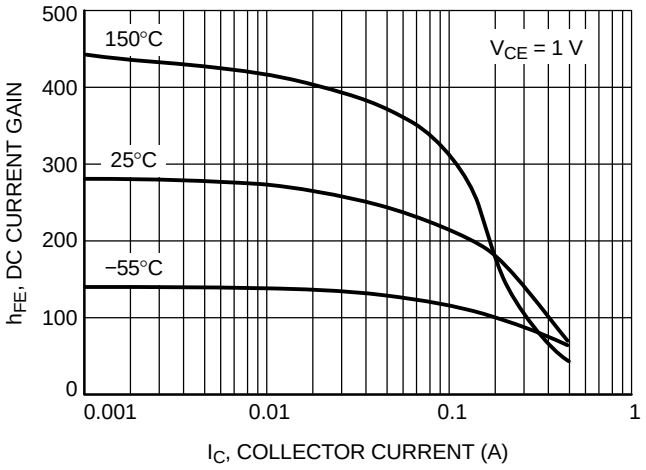


Figure 1. DC Current Gain vs. Collector Current

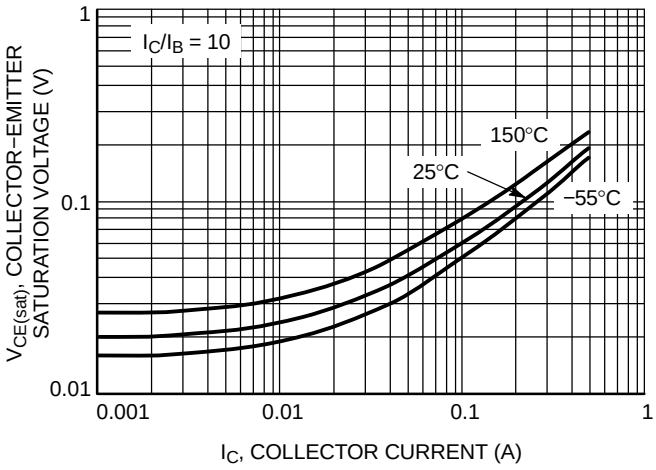


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

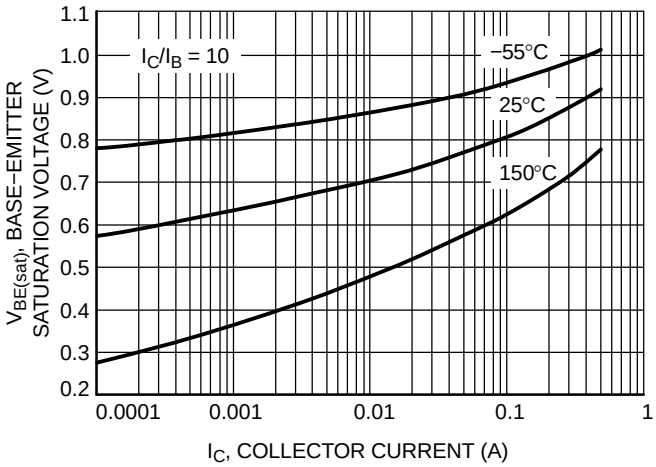


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

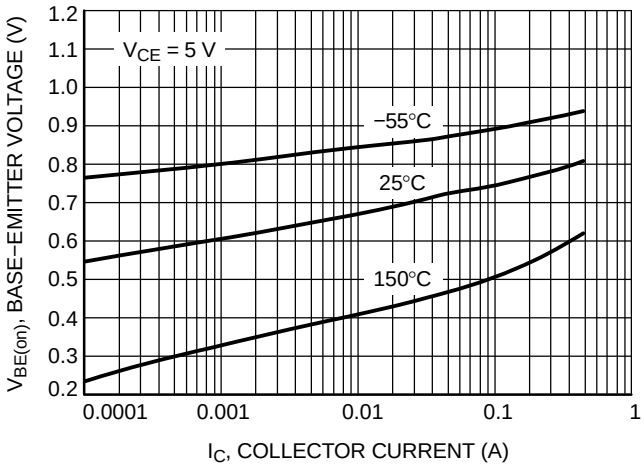


Figure 4. Base Emitter Voltage vs. Collector Current

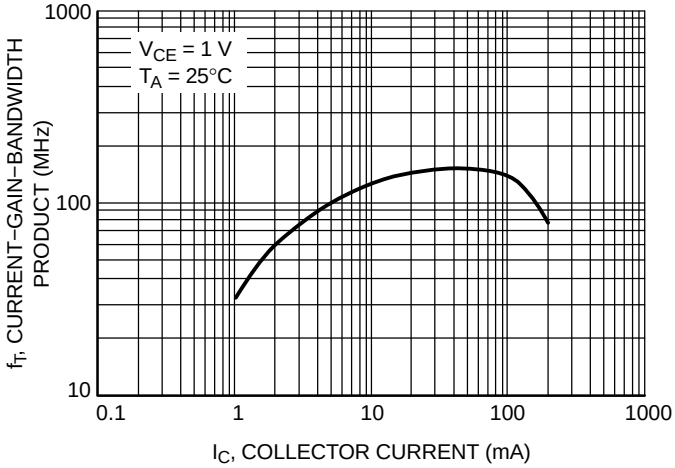


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS

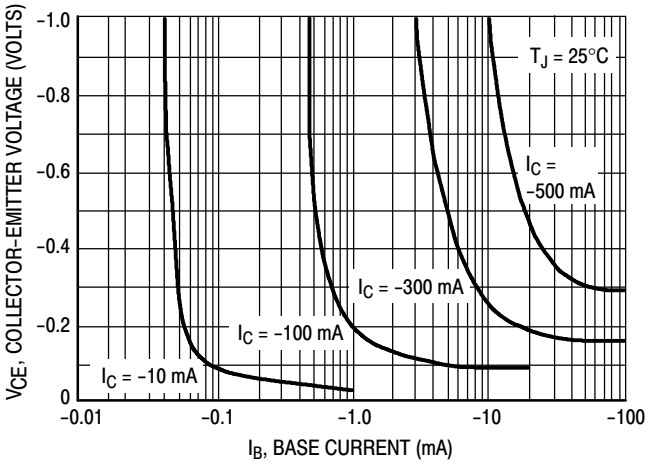


Figure 6. Saturation Region

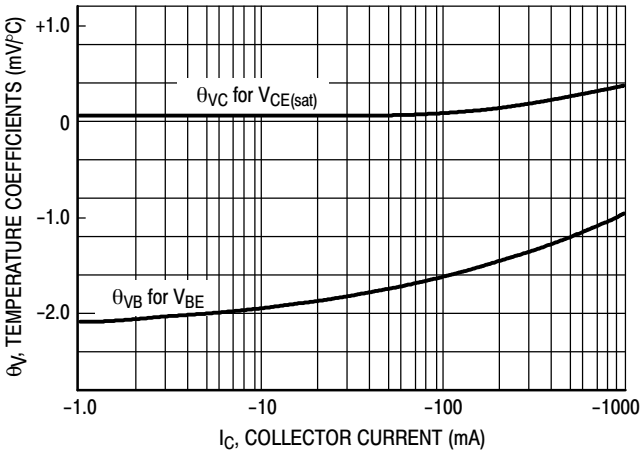


Figure 7. Temperature Coefficients

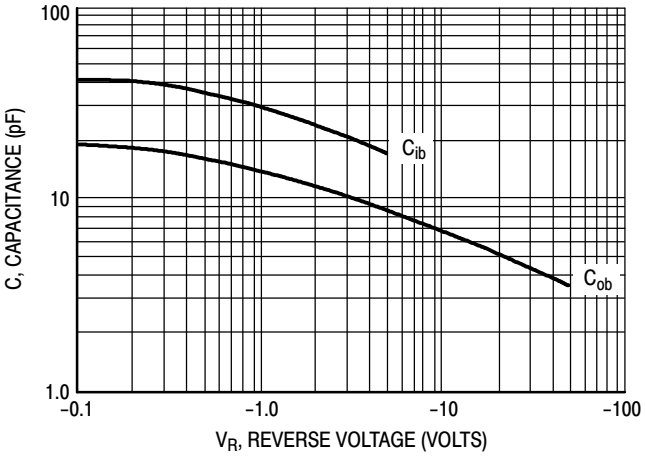
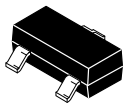


Figure 8. Capacitances

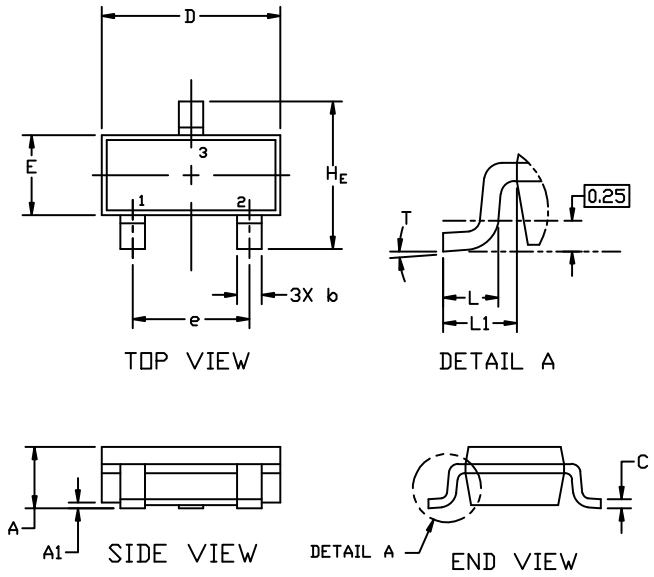
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 4:1

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

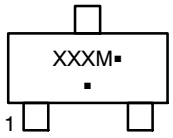


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

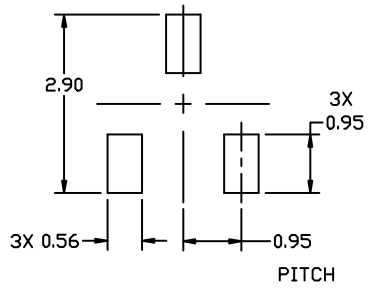
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOT−23 (TO−236)**		**PAGE 1 OF 2**

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

ADDITIONAL INFORMATION

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